

## Supplementary information: Polarisation-independent ultrafast laser selective etching processing in fused silica

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### 1 Etching rates for extended pulse repetition rates and energies as a function of the number of pulses

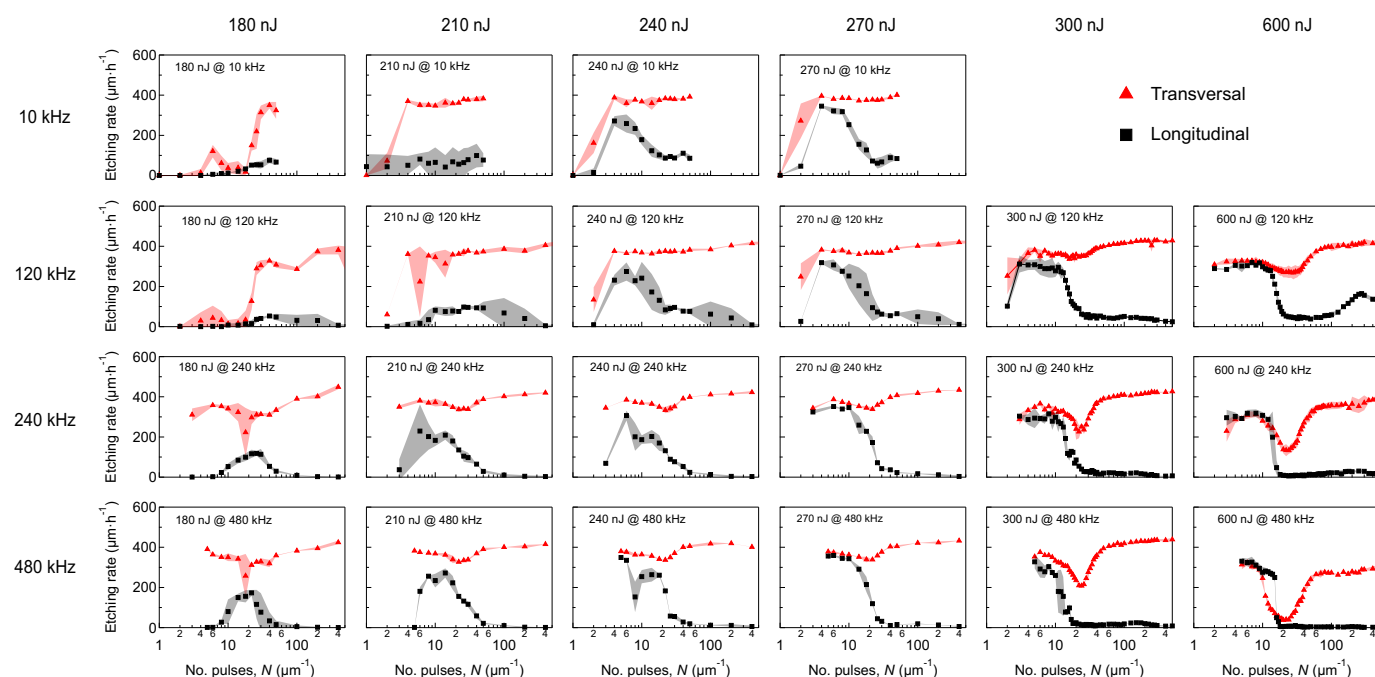


Fig. S1 Etching rates for transversal and longitudinal polarization for several pulse repetition rates and different pulse energies as a function of the number of pulses.

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## 2 Etching rates comparison between KOH and NaOH

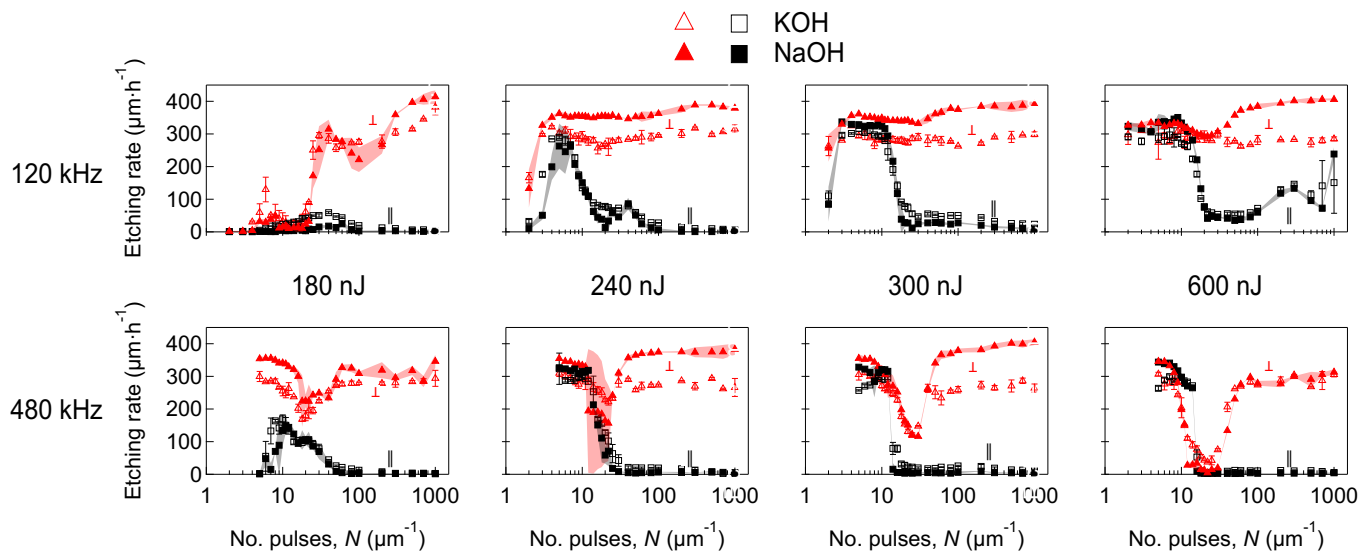


Fig. S2 Comparison of etching rates using two different etching solutions for different pulse energies and repetition rates. Both etching solutions yield similar etching rates and trends with the number of pulses, hence the mechanisms behind etching are likely the same. The highest etching rates correspond to the nanogratings regime for NaOH and by setting the polarisation perpendicular to the beam writing direction. Note that different samples than those of Figure S1 have been used for NaOH obtaining comparable results. Etching time was 4 hours for NaOH solution of 5 wt% and KOH of 40 wt%.

### 3 SEM results

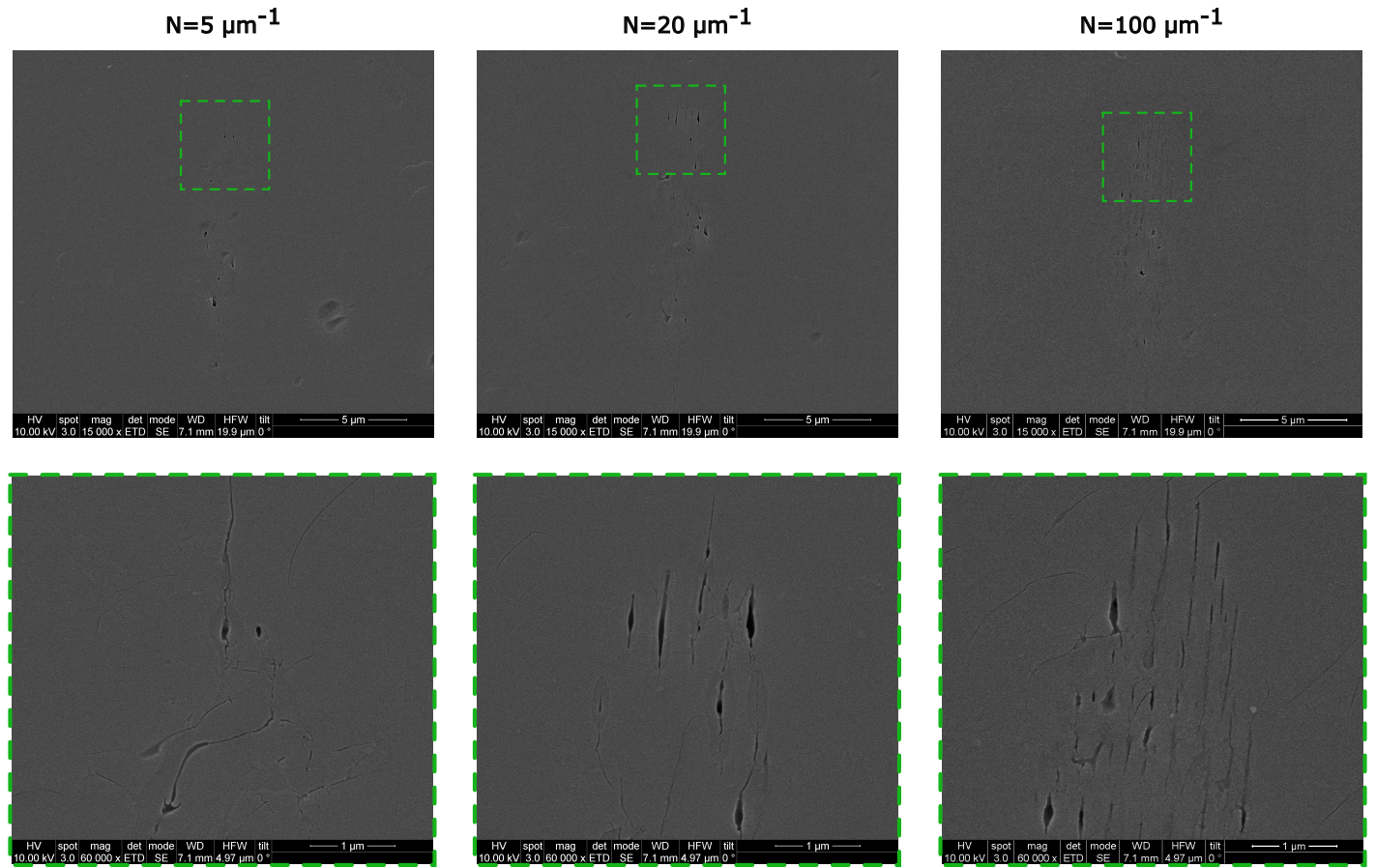


Fig. S3 SEM images of the cross section of laser affected zone using transversal polarization at 600 nJ and 120 kHz for pulses  $N=5$  (left),  $N=20$  (middle) and  $N=100 \mu\text{m}^{-1}$  (right). Green squares indicate the region shown in the bottom row images with higher magnification. After inscription, the sample was polished and etched for 2 minutes in NaOH solution (5 wt%).